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#### What is "Embedded - Microcontrollers"?

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#### Applications of "<u>Embedded -</u> <u>Microcontrollers</u>"

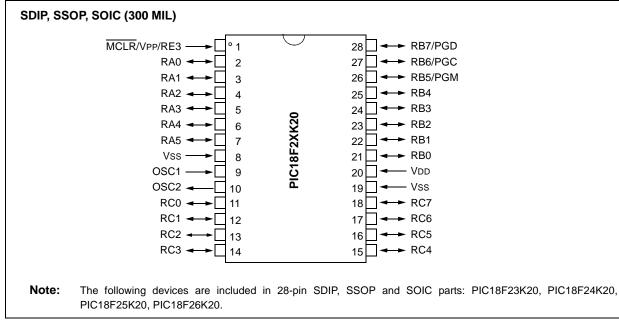
#### Details

Product Status	Active	
Core Processor	PIC	
Core Size	8-Bit	
Speed	64MHz	
Connectivity	I <sup>2</sup> C, SPI, UART/USART	
Peripherals	Brown-out Detect/Reset, HLVD, POR, PWM, WDT	
Number of I/O	35	
Program Memory Size	8KB (4K x 16)	
Program Memory Type	FLASH	
EEPROM Size	256 x 8	
RAM Size	512 x 8	
Voltage - Supply (Vcc/Vdd)	1.8V ~ 3.6V	
Data Converters	A/D 14x10b	
Oscillator Type	Internal	
Operating Temperature	-40°C ~ 85°C (TA)	
Mounting Type	Surface Mount	
Package / Case	44-VQFN Exposed Pad	
Supplier Device Package	44-QFN (8x8)	
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/pic18f43k20-i-ml	

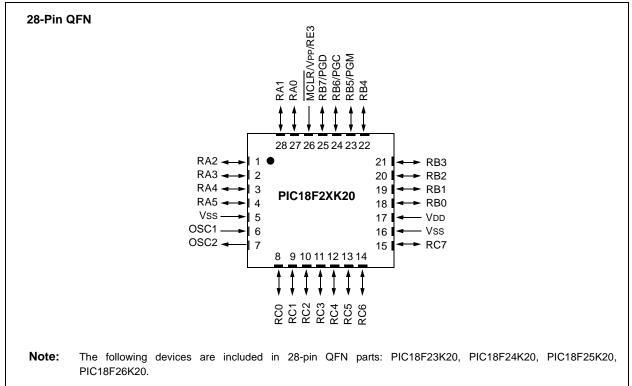
Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

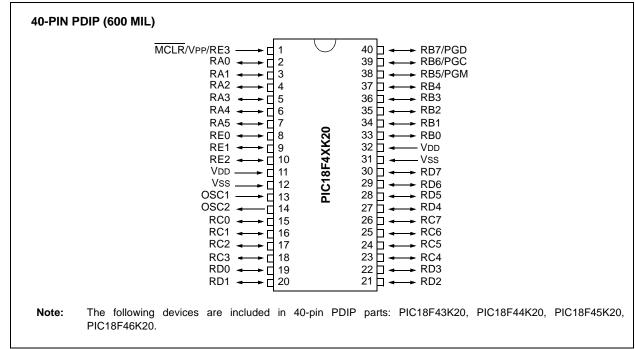
#### FIGURE 2-1: 28-PIN SDIP, SSOP AND SOIC PIN DIAGRAMS



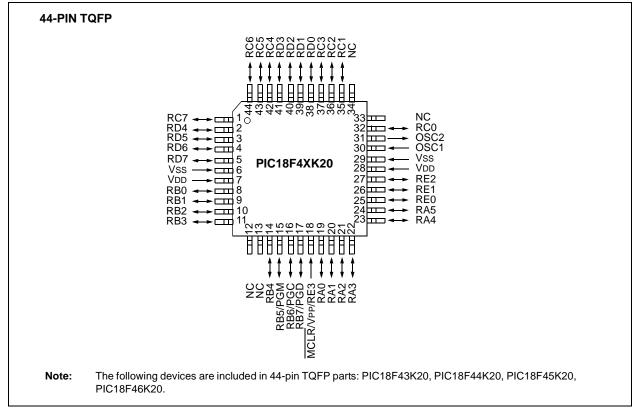




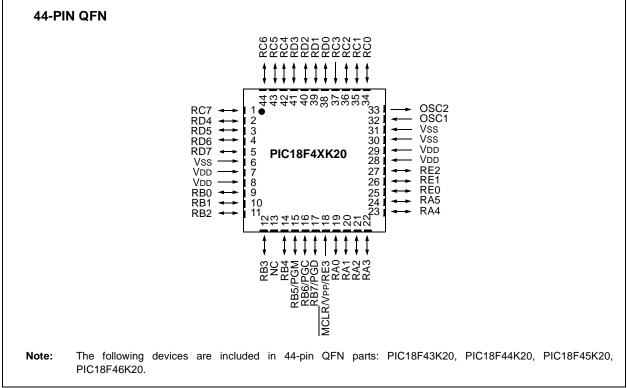
#### FIGURE 2-3: 40-PIN PDIP PIN DIAGRAMS



#### FIGURE 2-4: 44-PIN TQFP PIN DIAGRAMS





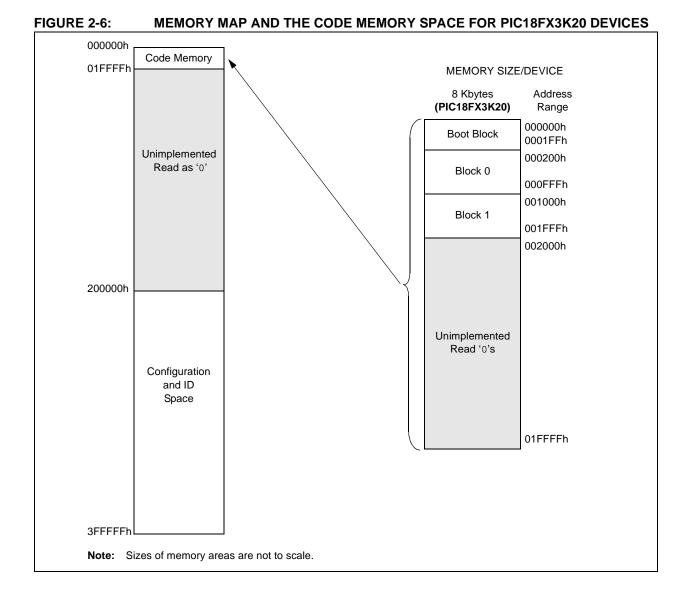


### 2.3 Memory Maps

For the PIC18FX3K20 devices, the code memory space extends from 0000h to 01FFFh (8 Kbytes) in two 4-Kbyte blocks. Addresses 0000h through 01FFh, however, define a "Boot Block" region that is treated separately from Block 0. All of these blocks define code protection boundaries within the code memory space.

## TABLE 2-2:IMPLEMENTATION OF CODE<br/>MEMORY

Device	Code Memory Size (Bytes)	
PIC18F23K20		
PIC18F43K20	000000h-001FFFh (8K)	



For PIC18FX5K20 devices, the code memory space extends from 000000h to 007FFFh (32 Kbytes) in four 8-Kbyte blocks. Addresses 000000h through 0007FFh, however, define a "Boot Block" region that is treated separately from Block 0. All of these blocks define code protection boundaries within the code memory space.

## TABLE 2-4:IMPLEMENTATION OF CODE<br/>MEMORY

Device	Code Memory Size (Bytes)
PIC18F25K20	000000h 007EEEh (22K)
PIC18F45K20	000000h-007FFFh (32K)

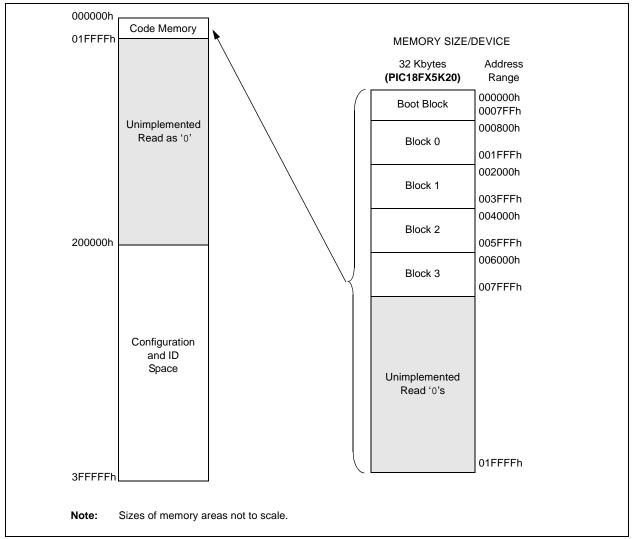


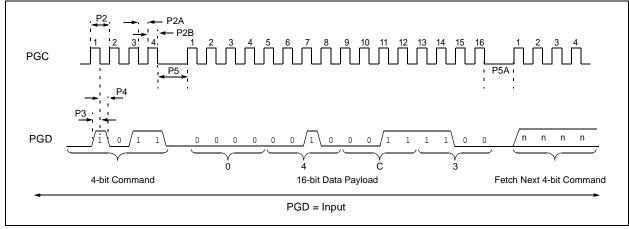
FIGURE 2-8: MEMORY MAP AND THE CODE MEMORY SPACE FOR PIC18FX5K20 DEVICES

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#### TABLE 2-7: SAMPLE COMMAND SEQUENCE

4-Bit Command	Data Payload	Core Instruction
1101		Table Write,
		post-increment by 2

#### FIGURE 2-16: TABLE WRITE, POST-INCREMENT TIMING DIAGRAM (1101)



## 3.0 DEVICE PROGRAMMING

Programming includes the ability to erase or write the various memory regions within the device.

In all cases, except high-voltage ICSP Bulk Erase, the EECON1 register must be configured in order to operate on a particular memory region.

When using the EECON1 register to act on code memory, the EEPGD bit must be set (EECON1<7> = 1) and the CFGS bit must be cleared (EECON1<6> = 0). The WREN bit must be set (EECON1<2> = 1) to enable writes of any sort (e.g., erases) and this must be done prior to initiating a write sequence. The FREE bit must be set (EECON1<4> = 1) in order to erase the program space being pointed to by the Table Pointer. The erase or write sequence is initiated by setting the WR bit (EECON1<1> = 1). It is strongly recommended that the WREN bit only be set immediately prior to a program or erase.

## 3.1 ICSP Erase

#### 3.1.1 HIGH-VOLTAGE ICSP BULK ERASE

Erasing code or data EEPROM is accomplished by configuring two Bulk Erase Control registers located at 3C0004h and 3C0005h. Code memory may be erased portions at a time, or the user may erase the entire device in one action. Bulk Erase operations will also clear any code-protect settings associated with the memory block erased. Erase options are detailed in Table 3-1. If data EEPROM is code-protected (CPD = 0), the user must request an erase of data EEPROM (e.g., 0084h as shown in Table 3-1).

Description	Data (3C0005h:3C0004h)
Chip Erase	0F8Fh
Erase User ID	0088h
Erase Data EEPROM	0084h
Erase Boot Block	0081h
Erase Config Bits	0082h
Erase Code EEPROM Block 0	0180h
Erase Code EEPROM Block 1	0280h
Erase Code EEPROM Block 2	0480h
Erase Code EEPROM Block 3	0880h

TABLE 3-1: BULK ERASE OPTIONS

The actual Bulk Erase function is a self-timed operation. Once the erase has started (falling edge of the 4th PGC after the NOP command), serial execution will cease until the erase completes (parameter P11). During this time, PGC may continue to toggle but PGD must be held low.

The code sequence to erase the entire device is shown in Table 3-2 and the flowchart is shown in Figure 3-1.

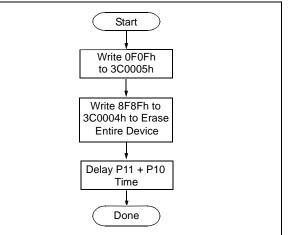
Note: A Bulk Erase is the only way to reprogram code-protect bits from an "on" state to an "off" state.

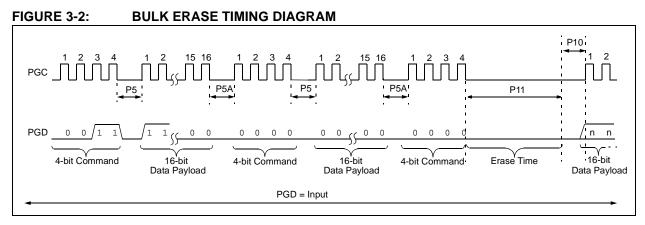
## TABLE 3-2: BULK ERASE COMMAND SEQUENCE

4-Bit Data			
Command	Payload	Core Instruction	
0000	0E 3C	MOVLW 3Ch	
0000	6E F8	MOVWF TBLPTRU	
0000	0E 00	MOVLW 00h	
0000	6E F7	MOVWF TBLPTRH	
0000	0E 05	MOVLW 05h	
0000	6E F6	MOVWF TBLPTRL	
1100	0F 0F	Write OFh to 3C0005h	
0000	0E 3C	MOVLW 3Ch	
0000	6E F8	MOVWF TBLPTRU	
0000	0E 00	MOVLW 00h	
0000	6E F7	MOVWF TBLPTRH	
0000	0E 04	MOVLW 04h	
0000	6E F6	MOVWF TBLPTRL	
1100	8F 8F	Write 8F8Fh TO 3C0004h to erase entire device.	
0000	00 00	NOP	
0000	00 00	Hold PGD low until erase completes.	

#### FIGURE 3-1:

**BULK ERASE FLOW** 





### 3.1.2 LOW-VOLTAGE ICSP BULK ERASE

When using low-voltage ICSP, the part must be supplied by the voltage specified in parameter D111 if a Bulk Erase is to be executed. All other Bulk Erase details as described above apply.

If it is determined that a program memory erase must be performed at a supply voltage below the Bulk Erase limit, refer to the erase methodology described in Section 3.1.3 "ICSP Row Erase" and Section 3.2.1 "Modifying Code Memory".

If it is determined that a data EEPROM erase must be performed at a supply voltage below the Bulk Erase limit, follow the methodology described in **Section 3.3** "**Data EEPROM Programming**" and write '1's to the array.

## 3.1.3 ICSP ROW ERASE

Regardless of whether high or low-voltage ICSP is used, it is possible to erase one row (64 bytes of data), provided the block is not code or write-protected. Rows are located at static boundaries beginning at program memory address 000000h, extending to the internal program memory limit (see **Section 2.3 "Memory Maps"**).

The Row Erase duration is self-timed. After the WR bit in EECON1 is set, two NOPs are issued. Erase starts upon the 4th PGC of the second NOP. It ends when the WR bit is cleared by hardware.

The code sequence to Row Erase a PIC18F2XK20/ 4XK20 device is shown in Table 3-3. The flowchart shown in Figure 3-3 depicts the logic necessary to completely erase a PIC18F2XK20/4XK20 device. The timing diagram for Row Erase is identical to the data EEPROM write timing shown in Figure 3-7.

**Note:** The TBLPTR register can point at any byte within the row intended for erase.

## 3.2 Code Memory Programming

Programming code memory is accomplished by first loading data into the write buffer and then initiating a programming sequence. The write and erase buffer sizes shown in Table 3-4 can be mapped to any location of the same size beginning at 000000h. The actual memory write sequence takes the contents of this buffer and programs the proper amount of code memory that contains the Table Pointer.

The programming duration is externally timed and is controlled by PGC. After a Start Programming command is issued (4-bit command, '1111'), a NOP is issued, where the 4th PGC is held high for the duration of the programming time, P9.

After PGC is brought low, the programming sequence is terminated. PGC must be held low for the time specified by parameter P10 to allow high-voltage discharge of the memory array.

The code sequence to program a PIC18F2XK20/ 4XK20 device is shown in Table 3-5. The flowchart shown in Figure 3-4 depicts the logic necessary to completely write a PIC18F2XK20/4XK20 device. The timing diagram that details the Start Programming command and parameters P9 and P10 is shown in Figure 3-5.

Note: The TBLPTR register must point to the same region when initiating the programming sequence as it did when the write buffers were loaded.

Devices (Arranged by Family)	Write Buffer Size (bytes)	Erase Size (bytes)
PIC18F26K20, PIC18F46K20	64	64
PIC18F24K20, PIC18F25K20, PIC18F44K20, PIC18F45K20	32	64
PIC18F23K20, PIC18F43K20	16	64

4-bit Command	Data Payload	Core Instruction	
Step 1: Direct a	ccess to code memor	y.	
0000 0000 0000	8E A6 9C A6 84 A6	BSF EECON1, EEPGD BCF EECON1, CFGS BSF EECON1, WREN	
Step 2: Point to	Step 2: Point to row to write.		
0000 0000 0000 0000 0000 0000	0E <addr[21:16]> 6E F8 0E <addr[15:8]> 6E F7 0E <addr[7:0]> 6E F6</addr[7:0]></addr[15:8]></addr[21:16]>	MOVLW <addr[21:16]> MOVWF TBLPTRU MOVLW <addr[15:8]> MOVWF TBLPTRH MOVLW <addr[7:0]> MOVWF TBLPTRL</addr[7:0]></addr[15:8]></addr[21:16]>	
Step 3: Load wr	Step 3: Load write buffer. Repeat for all but the last two bytes.		
1101	<msb><lsb></lsb></msb>	Write 2 bytes and post-increment address by 2.	
Step 4: Load write buffer for last two bytes and start programming.			
1111 0000	<msb><lsb> 00 00</lsb></msb>	Write 2 bytes and start programming. NOP - hold PGC high for time P9 and low for time P10.	
To continue writing data, repeat steps 2 through 4, where the Address Pointer is incremented by 2 at each iteration of the loop.			

#### TABLE 3-5: WRITE CODE MEMORY CODE SEQUENCE

#### 3.2.1 MODIFYING CODE MEMORY

The previous programming example assumed that the device has been Bulk Erased prior to programming (see **Section 3.1.1 "High-Voltage ICSP Bulk Erase"**). It may be the case, however, that the user wishes to modify only a section of an already programmed device.

The appropriate number of bytes required for the erase buffer must be read out of code memory (as described in **Section 4.2 "Verify Code Memory and ID Locations**") and buffered. Modifications can be made on this buffer. Then, the block of code memory that was read out must be erased and rewritten with the modified data.

The WREN bit must be set if the WR bit in EECON1 is used to initiate a write sequence.

4-bit Command	Data Payload	Core Instruction	
Step 1: Direct acc	ess to code memory.		
0000	8E A6	BSF EECON1, EEPGD	
0000	9C A6	BCF EECON1, CFGS	
Step 2: Read code	e memory into buffer (Section	on 4.1 "Read Code Memory, ID Locations and Configuration Bits").	
Step 3: Set the Ta	ble Pointer for the block to b	pe erased.	
0000	0E <addr[21:16]></addr[21:16]>	MOVLW <addr[21:16]></addr[21:16]>	
0000	6E F8	MOVWF TBLPTRU	
0000	0E <addr[8:15]></addr[8:15]>	MOVLW <addr[8:15]></addr[8:15]>	
0000	6E F7	MOVWF TBLPTRH	
0000	0E <addr[7:0]></addr[7:0]>	MOVLW <addr[7:0]></addr[7:0]>	
0000	6E F6	MOVWF TBLPTRL	
Step 4: Enable me	emory writes and setup an e	rase.	
0000	84 A6	BSF EECON1, WREN	
0000	88 A6	BSF EECON1, FREE	
Step 5: Initiate era	ise.		
0000	88 A6	BSF EECON1, FREE	
0000	82 A6	BSF EECON1, WR	
0000	00 00	NOP	
0000	00 00	NOP Erase starts on the 4th clock of this instruction	
Step 6: Poll WR b	it. Repeat until bit is clear.	•	
0000	50 A6	MOVF EECON1, W, 0	
0000	6E F5	MOVWF TABLAT	
0000	00 00	NOP	
0000	<msb><lsb></lsb></msb>	Shift out data <sup>(1)</sup>	
Step 7: Load write	buffer. The correct bytes w	ill be selected based on the Table Pointer.	
0000	0E <addr[21:16]></addr[21:16]>	MOVLW <addr[21:16]></addr[21:16]>	
0000	6E F8	MOVWF TBLPTRU	
0000	0E <addr[8:15]></addr[8:15]>	MOVLW <addr[8:15]></addr[8:15]>	
0000	6E F7	MOVWF TBLPTRH	
0000	0E <addr[7:0]></addr[7:0]>	MOVLW <addr[7:0]></addr[7:0]>	
0000	6E F6	MOVWF TBLPTRL	
1101	<msb><lsb></lsb></msb>	Write 2 bytes and post-increment address by 2.	
•	•	-	
•	•	Repeat as many times as necessary to fill the write buffer	
•	•	Write 2 bytes and start programming.	
1111	<msb><lsb></lsb></msb>	NOP - hold PGC high for time P9 and low for time P10.	
0000	00 00		
To continue modifying data, repeat Steps 2 through 6, where the Address Pointer is incremented by the appropriate number of bytes (see Table 3-4) at each iteration of the loop. The write cycle must be repeated enough times to completely rewrite the contents of the erase buffer.			
Step 8: Disable wi	rites.		
0000	94 A6	BCF EECON1, WREN	

#### TABLE 3-6: MODIFYING CODE MEMORY

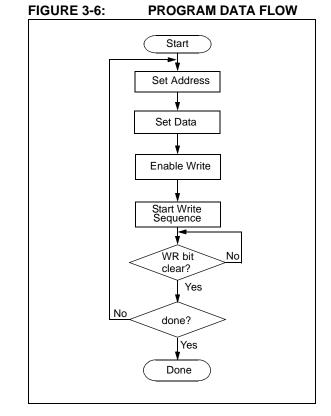
### 3.3 Data EEPROM Programming

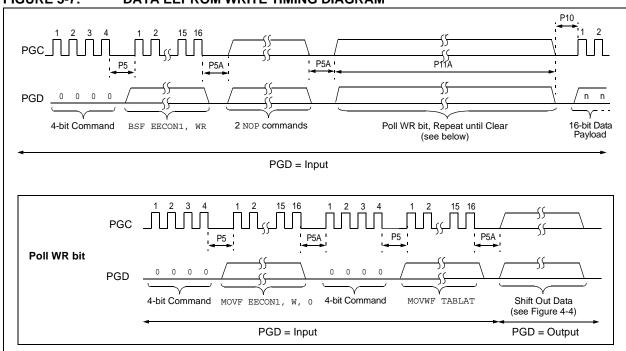
Data EEPROM is accessed one byte at a time via an Address Pointer (register pair EEADRH:EEADR) and a data latch (EEDATA). Data EEPROM is written by loading EEADRH:EEADR with the desired memory location, EEDATA with the data to be written and initiating a memory write by appropriately configuring the EECON1 register. A byte write automatically erases the location and writes the new data (erase-before-write).

When using the EECON1 register to perform a data EEPROM write, both the EEPGD and CFGS bits must be cleared (EECON1<7:6> = 00). The WREN bit must be set (EECON1<2> = 1) to enable writes of any sort and this must be done prior to initiating a write sequence. The write sequence is initiated by setting the WR bit (EECON1<1> = 1).

The write begins on the falling edge of the 24th PGC after the WR bit is set. It ends when the WR bit is cleared by hardware.

After the programming sequence terminates, PGC must be held low for the time specified by parameter P10 to allow high-voltage discharge of the memory array.





#### FIGURE 3-7: DATA EEPROM WRITE TIMING DIAGRAM

## 4.0 READING THE DEVICE

#### 4.1 Read Code Memory, ID Locations and Configuration Bits

Code memory is accessed one byte at a time via the 4-bit command, '1001' (table read, post-increment). The contents of memory pointed to by the Table Pointer (TBLPTRU:TBLPTRH:TBLPTRL) are serially output on PGD.

The 4-bit command is shifted in LSb first. The read is executed during the next 8 clocks, then shifted out on PGD during the last 8 clocks, LSb to MSb. A delay of P6 must be introduced after the falling edge of the 8th

TABLE 4-1:	READ CODE MEMORY SEQUENCE
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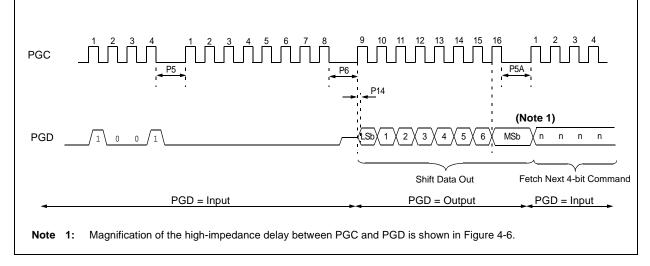
PGC of the operand to allow PGD to transition from an input to an output. During this time, PGC must be held low (see Figure 4-1). This operation also increments the Table Pointer by one, pointing to the next byte in code memory for the next read.

This technique will work to read any memory in the 000000h to 3FFFFFh address space, so it also applies to the reading of the ID and Configuration registers.

**Note:** When table read protection is enabled, the first read access to a protected block should be discarded and the read repeated to retrieve valid data. Subsequent reads of the same block can be performed normally.

4-bit Command	Data Payload	Core Instruction
Step 1: Set Tabl	e Pointer	
0000	0E <addr[21:16]></addr[21:16]>	MOVLW Addr[21:16]
0000	6E F8	MOVWF TBLPTRU
0000	0E <addr[15:8]></addr[15:8]>	MOVLW <addr[15:8]></addr[15:8]>
0000	6E F7	MOVWF TBLPTRH
0000	0E <addr[7:0]></addr[7:0]>	MOVLW <addr[7:0]></addr[7:0]>
0000	6E F6	MOVWF TBLPTRL
Step 2: Read memory and then shift out on PGD, LSb to MSb		
1001	00 00	TBLRD *+

FIGURE 4-1: TABLE READ POST-INCREMENT INSTRUCTION TIMING DIAGRAM (1001)



### 4.3 Verify Configuration Bits

A configuration address may be read and output on PGD via the 4-bit command, '1001'. Configuration data is read and written in a byte-wise fashion, so it is not necessary to merge two bytes into a word prior to a compare. The result may then be immediately compared to the appropriate configuration data in the programmer's memory for verification. Refer to **Section 4.1 "Read Code Memory, ID Locations and Configuration Bits"** for implementation details of reading configuration data.

#### 4.4 Read Data EEPROM Memory

Data EEPROM is accessed one byte at a time via an Address Pointer (register pair EEADRH:EEADR) and a data latch (EEDATA). Data EEPROM is read by loading EEADRH:EEADR with the desired memory location and initiating a memory read by appropriately configuring the EECON1 register. The data will be loaded into EEDATA, where it may be serially output on PGD via the 4-bit command, '0010' (Shift Out Data Holding register). A delay of P6 must be introduced after the falling edge of the 8th PGC of the operand to allow PGD to transition from an input to an output. During this time, PGC must be held low (see Figure 4-4).

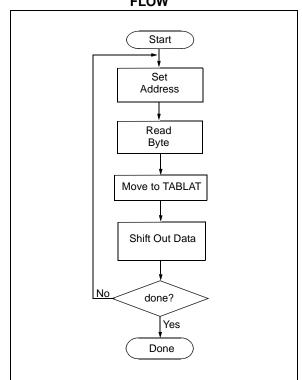
The command sequence to read a single byte of data is shown in Table 4-2.

4-bit Command	Data Payload	Core Instruction				
Step 1: Direct acc	ess to data EEPROM.					
0000	9E A6 9C A6	BCF EECON1, EEPGD BCF EECON1, CFGS				
Step 2: Set the da	ata EEPROM Address Point	er.				
0000 0000 0000 0000	0E <addr> 6E A9 OE <addrh> 6E AA</addrh></addr>	MOVLW <addr> MOVWF EEADR MOVLW <addrh> MOVWF EEADRH</addrh></addr>				
Step 3: Initiate a memory read.						
0000	80 A6	BSF EECON1, RD				
Step 4: Load data into the Serial Data Holding register.						
0000 0000 0000 0010	50 A8 6E F5 00 00 <msb><lsb></lsb></msb>	MOVF EEDATA, W, O MOVWF TABLAT NOP Shift Out Data <sup>(1)</sup>				

#### TABLE 4-2: READ DATA EEPROM MEMORY

**Note 1:** The <LSB> is undefined. The <MSB> is the data.

### FIGURE 4-3: READ DATA EEPROM FLOW



## 5.3 Single-Supply ICSP Programming

The LVP bit in Configuration register, CONFIG4L, enables Single-Supply (Low-Voltage) ICSP Programming. The LVP bit defaults to a '1' (enabled) from the factory.

If Single-Supply Programming mode is not used, the LVP bit can be programmed to a '0' and RB5/PGM becomes a digital I/O pin. However, the LVP bit may only be programmed by entering the High-Voltage ICSP mode, where MCLR/VPP/RE3 is raised to VIHH. Once the LVP bit is programmed to a '0', only the High-Voltage ICSP mode is available and only the High-Voltage ICSP mode can be used to program the device.

- Note 1: The High-Voltage ICSP mode is always available, regardless of the state of the LVP bit, by applying VIHH to the MCLR/ VPP/RE3 pin.
  - 2: While in Low-Voltage ICSP mode, the RB5 pin can no longer be used as a general purpose I/O.

### 5.4 Embedding Configuration Word Information in the HEX File

To allow portability of code, a PIC18F2XK20/4XK20 programmer is required to read the Configuration Word locations from the hex file. If Configuration Word information is not present in the hex file, then a simple warning message should be issued. Similarly, while saving a hex file, all Configuration Word information must be included. An option to not include the Configuration Word information may be provided. When embedding Configuration Word information in the hex file, it should start at address 300000h.

Microchip Technology Inc. feels strongly that this feature is important for the benefit of the end customer.

#### 5.5 Embedding Data EEPROM Information In the HEX File

To allow portability of code, a PIC18F2XK20/4XK20 programmer is required to read the data EEPROM information from the hex file. If data EEPROM information is not present, a simple warning message should be issued. Similarly, when saving a hex file, all data EEPROM information must be included. An option to not include the data EEPROM information may be provided. When embedding data EEPROM information in the hex file, it should start at address F00000h.

Microchip Technology Inc. believes that this feature is important for the benefit of the end customer.

## 5.6 Checksum Computation

The checksum is calculated by summing the following:

- The contents of all code memory locations
- The Configuration Word, appropriately masked
- ID locations (Only if any portion of program memory is code-protected)

The Least Significant 16 bits of this sum are the checksum.

Code protection limits access to program memory by both external programmer (code-protect) and code execution (table read protect). The ID locations, when included in a code protected checksum, contain the checksum of an unprotected part. The unprotected checksum is distributed: one nibble per ID location. Each nibble is right justified.

Table 5-4 describes how to calculate the checksum for each device.

**Note:** The checksum calculation differs depending on the code-protect setting. Since the code memory locations read out differently depending on the code-protect setting, the table describes how to manipulate the actual code memory values to simulate the values that would be read from a protected device. When calculating a checksum by reading a device, the entire code memory can simply be read and summed. The Configuration Word and ID locations can always be read.

Device	Code- Protect	Blank Value	0xAA at 0 and Max Address	
	None	SUM[0000:01FF]+SUM[0200:0FFF]+SUM[1000:1FFF]+ (CONFIG1L & 00h)+(CONFIG1H & CFh)+(CONFIG2L & 1Fh)+ (CONFIG2H & 1F)+(CONFIG3L & 00h)+(CONFIG3H & 8Fh)+ (CONFIG4L & C5h)+(CONFIG4H & 00h)+(CONFIG5L & 03h)+ (CONFIG5H & C0h)+(CONFIG6L & 03h)+(CONFIG6H & E0h)+ (CONFIG7L & 03h)+(CONFIG7H & 40h)	E33Eh	E294h
PIC18FX3K20	Boot Block	SUM[0200:0FFF]+SUM[1000:1FFF]+(CONFIG1L & 00h)+ (CONFIG1H & CFh)+(CONFIG2L & 1Fh)+(CONFIG2H & 1F)+ (CONFIG3L & 00h)+(CONFIG3H & 8Fh)+(CONFIG4L & C5h)+ (CONFIG4H & 00h)+(CONFIG5L & 03h)+(CONFIG5H & C0h)+ (CONFIG6L & 03h)+(CONFIG6H & E0h)+(CONFIG7L & 03h)+ (CONFIG7H & 40h)+SUM_ID	E520h	E4C6h
	Boot/ Block 0	SUM[1000:1FFF]+(CONFIG1L & 00h)+(CONFIG1H & CFh)+ (CONFIG2L & 1Fh)+(CONFIG2H & 1F)+(CONFIG3L & 00h)+ (CONFIG3H & 8Fh)+(CONFIG4L & C5h)+(CONFIG4H & 00h)+ (CONFIG5L & 03h)+(CONFIG5H & C0h)+(CONFIG6L & 03h)+ (CONFIG6H & E0h)+(CONFIG7L & 03h)+(CONFIG7H & 40h)+SUM_ID	F31Fh	F2C5h
	All	(CONFIG1L & 00h)+(CONFIG1H & CFh)+(CONFIG2L & 1Fh)+ (CONFIG2H & 1F)+(CONFIG3L & 00h)+(CONFIG3H & 8Fh)+ (CONFIG4L & C5h)+(CONFIG4H & 00h)+(CONFIG5L & 03h)+ (CONFIG5H & C0h)+(CONFIG6L & 03h)+(CONFIG6H & E0h)+ (CONFIG7L & 03h)+(CONFIG7H & 40h)+SUM_ID	031Dh	0318h
	None	SUM[0000:07FF]+SUM[0800:1FFF]+SUM[2000:3FFF]+ (CONFIG1L & 00h)+(CONFIG1H & CFh)+(CONFIG2L & 1Fh)+ (CONFIG2H & 1F)+(CONFIG3L & 00h)+(CONFIG3H & 8Fh)+ (CONFIG4L & C5h)+(CONFIG4H & 00h)+(CONFIG5L & 03h)+ (CONFIG5H & C0h)+(CONFIG6L & 03h)+(CONFIG6H & E0h)+ (CONFIG7L & 03h)+(CONFIG7H & 40h)	C33Eh	C294h
PIC18FX4K20	Boot Block	SUM[0800:1FFF]+SUM[2000:3FFF]+(CONFIG1L & 00h)+ (CONFIG1H & CFh)+(CONFIG2L & 1Fh)+(CONFIG2H & 1F)+ (CONFIG3L & 00h)+(CONFIG3H & 8Fh)+(CONFIG4L & C5h)+ (CONFIG4H & 00h)+(CONFIG5L & 03h)+(CONFIG5H & C0h)+ (CONFIG6L & 03h)+(CONFIG6H & E0h)+(CONFIG7L & 03h)+ (CONFIG7H & 40h)+SUM_ID	CB1Eh	CAC4h
	Boot/ Block 0			E2C3h
	All	(CONFIG1L & 00h)+(CONFIG1H & CFh)+(CONFIG2L & 1Fh)+ (CONFIG2H & 1F)+(CONFIG3L & 00h)+(CONFIG3H & 8Fh)+ (CONFIG4L & C5h)+(CONFIG4H & 00h)+(CONFIG5L & 03h)+ (CONFIG5H & C0h)+(CONFIG6L & 03h)+(CONFIG6H & E0h)+ (CONFIG7L & 03h)+(CONFIG7H & 40h)+SUM_ID	031Bh	0316h
SUN	NFIGx = 0 //[a:b] = 3 //_ID = 1	<u>Description</u> Configuration Word Sum of locations, a to b inclusive Byte-wise sum of lower four bits of all customer ID locations Addition		

+ = Addition & = Bit-wise AND

## TABLE 5-4: CHECKSUM COMPUTATION (CONTINUED)

Device	Code- Protect	Checksum	Blank Value	0xAA at 0 and Max Address
	None	SUM[0000:07FF]+SUM[0800:1FFF]+SUM[2000:3FFF]+ SUM[4000:5FFF]+SUM[6000:7FFF]+(CONFIG1L & 00h)+ (CONFIG1H & CFh)+(CONFIG2L & 1Fh)+(CONFIG2H & 1F)+ (CONFIG3L & 00h)+(CONFIG3H & 8Fh)+(CONFIG4L & C5h)+ (CONFIG4H & 00h)+(CONFIG5L & 0Fh)+(CONFIG5H & C0h)+ (CONFIG6L & 0Fh)+(CONFIG6H & E0h)+(CONFIG7L & 0Fh)+ (CONFIG7H & 40h)	8362h	82B8h
PIC18FX5K20	Boot Block	SUM[0800:1FFF]+SUM[2000:3FFF]+SUM[4000:5FFF]+SUM[6000:7FFF ]+ (CONFIG1L & 00h)+(CONFIG1H & CFh)+(CONFIG2L & 1Fh)+ (CONFIG2H & 1F)+(CONFIG3L & 00h)+(CONFIG3H & 8Fh)+ (CONFIG4L & C5h)+(CONFIG4H & 00h)+(CONFIG5L & 0Fh)+ (CONFIG5H & C0h)+(CONFIG6L & 0Fh)+(CONFIG6H & E0h)+ (CONFIG7L & 0Fh)+(CONFIG7H & 40h)+SUM_ID	8B35h	8AEAh
	Boot/ Block 0/ Block 1	SUM[4000:5FFF]+SUM[6000:7FFF]+(CONFIG1L & 00h)+ (CONFIG1H & CFh)+(CONFIG2L & 1Fh)+(CONFIG2H & 1F)+ (CONFIG3L & 00h)+(CONFIG3H & 8Fh)+(CONFIG4L & C5h)+ (CONFIG4H & 00h)+(CONFIG5L & 0Fh)+(CONFIG5H & C0h)+ (CONFIG6L & 0Fh)+(CONFIG6H & E0h)+(CONFIG7L & 0Fh)+ (CONFIG7H & 40h)+SUM_ID	C332h	C2E7h
	All	(CONFIG1L & 00h)+(CONFIG1H & CFh)+(CONFIG2L & 1Fh)+ (CONFIG2H & 1F)+(CONFIG3L & 00h)+(CONFIG3H & 8Fh)+ (CONFIG4L & C5h)+(CONFIG4H & 00h)+(CONFIG5L & 0Fh)+ (CONFIG5H & C0h)+(CONFIG6L & 0Fh)+(CONFIG6H & E0h)+ (CONFIG7L & 0Fh)+(CONFIG7H & 40h)+SUM_ID	0326h	0330h
SUN	NFIGx = 0 //[a:b] = 5	Description Configuration Word Sum of locations, a to b inclusive		

SUM\_ID = Byte-wise sum of lower four bits of all customer ID locations

+ = Addition

& = Bit-wise AND

Device	Code- Protect	Checksum	Blank Value	0xAA at 0 and Max Address
	None	SUM[0000:07FF]+SUM[0800:3FFF]+SUM[4000:7FFF]+ SUM[8000:BFFF]+SUM[C000:FFFF]+(CONFIG1L & 00h)+ (CONFIG1H & CFh)+(CONFIG2L & 1Fh)+(CONFIG2H & 1F)+ (CONFIG3L & 00h)+(CONFIG3H & 8Fh)+(CONFIG4L & C5h)+ (CONFIG4H & 00h)+(CONFIG5L & 0Fh)+(CONFIG5H & C0h)+ (CONFIG6L & 0Fh)+(CONFIG6H & E0h)+(CONFIG7L & 0Fh)+ (CONFIG7H & 40h)	0362h	02B8h
PIC18FX6K2	Boot Block	SUM[0800:3FFF]+SUM[4000:7FFF]+SUM[8000:BFFF]+SUM[C000:FFF F]+ (CONFIG1L & 00h)+(CONFIG1H & CFh)+(CONFIG2L & 1Fh)+ (CONFIG2H & 1F)+(CONFIG3L & 00h)+(CONFIG3H & 8Fh)+ (CONFIG4L & C5h)+(CONFIG4H & 00h)+(CONFIG5L & 0Fh)+ (CONFIG5H & C0h)+(CONFIG6L & 0Fh)+(CONFIG6H & E0h)+ (CONFIG7L & 0Fh)+(CONFIG7H & 40h)+SUM_ID	0B2Dh	0AE2h
	Boot/ Block 0/ Block 1	SUM[3000:BFFF]+SUM[C000:FFFF]+(CONFIG1L & 00h)+ (CONFIG1H & CFh)+(CONFIG2L & 1Fh)+(CONFIG2H & 1F)+ (CONFIG3L & 00h)+(CONFIG3H & 8Fh)+(CONFIG4L & C5h)+ (CONFIG4H & 00h)+(CONFIG5L & 0Fh)+(CONFIG5H & C0h)+ (CONFIG6L & 0Fh)+(CONFIG6H & E0h)+(CONFIG7L & 0Fh)+ (CONFIG7H & 40h)+SUM_ID	832Ah	82DFh
	All	(CONFIG1L & 00h)+(CONFIG1H & CFh)+(CONFIG2L & 1Fh)+ (CONFIG2H & 1F)+(CONFIG3L & 00h)+(CONFIG3H & 8Fh)+ (CONFIG4L & C5h)+(CONFIG4H & 00h)+(CONFIG5L & 0Fh)+ (CONFIG5H & C0h)+(CONFIG6L & 0Fh)+(CONFIG6H & E0h)+ (CONFIG7L & 0Fh)+(CONFIG7H & 40h)+SUM_ID	031Eh	0328h
C SI SI	CONFIGx = Configuration Word SUM[a:b] = Sum of locations, a to b inclusive SUM_ID = Byte-wise sum of lower four bits of all customer ID locations			
+				

& = Bit-wise AND

## 6.0 AC/DC CHARACTERISTICS TIMING REQUIREMENTS FOR PROGRAM/ VERIFY TEST MODE (CONTINUED)

Standard Operating Conditions Operating Temperature: 25°C is recommended						
Param No.	Sym.	Characteristic		Max.	Units	Conditions
P12	THLD2	Input Data Hold Time from MCLR/VPP/RE3 ↑	2	—	μS	
P13	TSET2	VDD ↑ Setup Time to MCLR/VPP/RE3 ↑	100	—	ns	
P14	TVALID	Data Out Valid from PGC $\uparrow$	10	—	ns	
P15	TSET3	PGM <sup>↑</sup> Setup Time to MCLR/VPP/RE3 <sup>↑</sup>	2	—	μS	
P16	TDLY8	Delay between Last PGC $\downarrow$ and $\overline{MCLR}/VPP/RE3\downarrow$	0	—	S	
P17	Thld3	MCLR/VPP/RE3 ↓ to VDD ↓	—	100	ns	
P18	THLD4	MCLR/VPP/RE3 ↓ to PGM ↓	0	_	S	
P19	Thiz	Delay from PGC ↑ to PGD High-Z	3	10	nS	
P20	TPPDP	Hold time after VPP changes	5	_	μS	

**Note 1:** Do not allow excess time when transitioning MCLR between VIL and VIHH; this can cause spurious program executions to occur. The maximum transition time is:

1 TCY + TPWRT (if enabled) + 1024 Tosc (for LP, HS, HS/PLL and XT modes only) + 2 ms (for HS/PLL mode only) + 1.5 μs (for EC mode only) where TCY is the instruction cycle time, TPWRT is the Power-up Timer period and Tosc is the oscillator period. For specific values, refer to the Electrical Characteristics section of the device data sheet for the particular device.

NOTES:



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